





MBR260HW SURFACE MOUNT SCHOTTKY BARRIER DIODE



Features

- 125 ° C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request
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Circuit Diagram



Mechanical Data

- Case: SOD-123, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202,
 - Method 208
- Polarity: Cathode Band
- Weight: 0.01 grams(approx)

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current (At Rated V _R , T _L = 55° C)	lo	2	Α
Forward Voltage	V _{FM}	0.52 0.66	V
Peak Reverse Current @T _A = 25°C	I _{RM}	50	μΑ
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half-wave, Single Phase, 60 Hz)	I _{FSM}	30	А
Maximum Junction Capacitance (Note 1)	Cj	100	pF
Operating Junction Temperature Range	TJ	125	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Note 1. Measured at 1MHz and applied reverse voltage of 5.0V D.C.

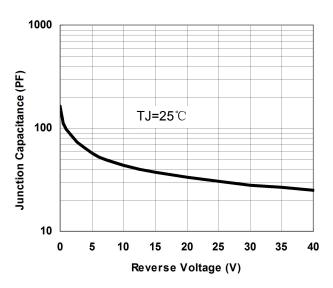
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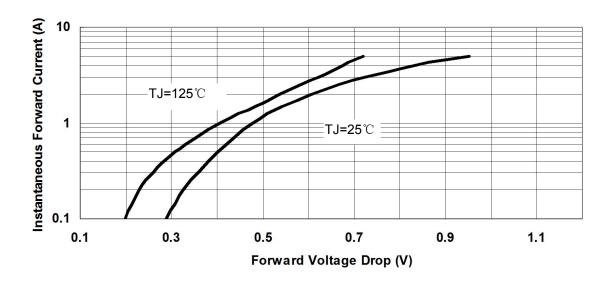
Ratings and Characteristics Curves



0.1 TJ=125°C 0.01 TJ=25°C 0.01 TJ=25°C 0.001 0.001 0.001 TJ=25°C 0.001 0

Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics



100

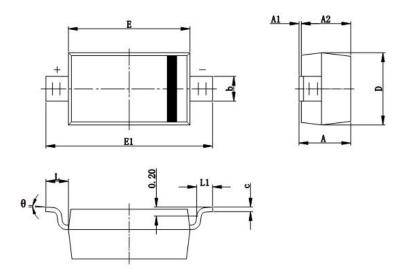
Fig.3-Typical Forward Voltage Drop Characteristics







Mechanical Dimensions SOD-123



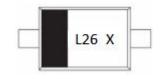
Millimeters		Inches		
SYMBOL	MIN.	MAX.	MIN.	MAX.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
Е	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF.		0.020 REF.	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Ordering Information

Device	Package	Shipping
MBR260HW	SOD-123 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

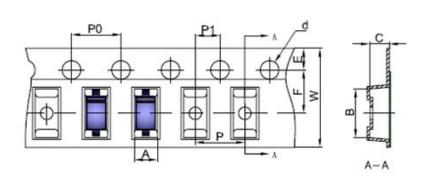


Where X is Date Code

L26 = Part Name

MBR260HW

Carrier Tape Specification SOD-123



SYMBOL	Millimeters		
STIMBUL	Min.	Max.	
Α	1.80	1.90	
В	3.89	3.99	
С	1.52	1.62	
d	1.45	1.65	
Е	1.65	1.85	
F	3.40	3.60	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
W	7.90	8.30	

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